Converter - Brake - Inverter Module (CBI2)
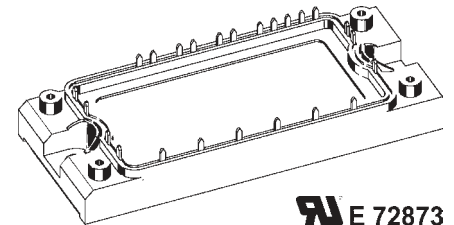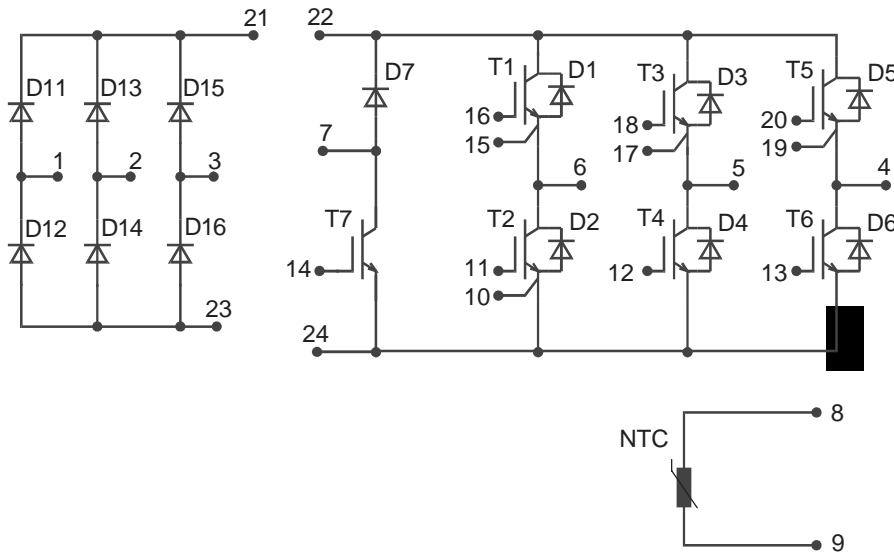
UL E 72873

B4

Three Phase Rectifier	Brake Chopper	Three Phase Inverter
V_{RRM} = 1600V	V_{CES} = 1200 V	V_{CES} = 1200 V
I_{DAVM} = 26 A	I_{C25} = 20 A	I_{C25} = 20 A
I_{FSM} = 160 A	$V_{CE(sat)}$ = 2.3 V	$V_{CE(sat)}$ = 2.3 V

Input Rectifier Bridge D11 - D16

Symbol	Conditions	Maximum Ratings	
V_{RRM}		1600	V
I_{FAV}	T_C = 80°C; sine 180°	19	A
I_{DAVM}	T_C = 80°C; rectangular; d = 1/3	18	A
I_{FSM}	T_{VJ} = 25°C; t = 10 ms; sine 50 Hz	160	A
P_{tot}	T_C = 25°C	85	W

Symbol	Conditions	Characteristic Values (T_{VJ} = 25°C, unless otherwise specified)			
		min.	typ.	max.	
V_F	I_F = 10 A; T_{VJ} = 25°C		1.3	1.6	V
	T_{VJ} = 125°C		1.3		V
I_R	V_R = V_{RRM}; T_{VJ} = 25°C			0.1	mA
	T_{VJ} = 125°C		1		mA
t_{rr}	V_R = 100 V; I_F = 10 A; di/dt = -10 A/µs		1		µs
R_{thJC}	(per diode)			1.47	K/W

Application: AC motor drives with

- Input from single or three phase grid
- Three phase synchronous or asynchronous motor
- electric braking operation

Features

- High level of integration - only one power semiconductor module required for the whole drive
- Fast rectifier diodes for enhanced EMC behaviour
- NPT IGBT technology with low saturation voltage, low switching losses, high RBSOA and short circuit ruggedness
- Epitaxial free wheeling diodes with Hiperfast and soft reverse recovery
- Industry standard package with insulated copper base plate and soldering pins for PCB mounting
- Temperature sense included

IXYS reserves the right to change limits, test conditions and dimensions.

B4

Output Inverter T1 - T6

Symbol	Conditions		Maximum Ratings	
V_{CES}	T_{VJ} = 25°C to 150°C		1200	V
V_{GES}	Continuous		± 20	V
V_{GEM}	Transient		± 30	V
I_{C25}	T_C = 25°C		20	A
I_{C80}	T_C = 80°C		15	A
RBSOA	V_{GE} = ±15 V; R_G = 82 Ω; T_{VJ} = 125°C Clamped inductive load; L = 100 µH	I_{CM} = $V_{CEK} \leq V_{CES}$	20	A
t_{SC} (SCSOA)	V_{CE} = 720 V; V_{GE} = ±15 V; R_G = 82 Ω; T_{VJ} = 125°C non-repetitive		10	µs
P_{tot}	T_C = 25°C		105	W

Symbol	Conditions	Characteristic Values (T_{VJ} = 25°C, unless otherwise specified)			
		min.	typ.	max.	
$V_{CE(sat)}$	I_C = 10 A; V_{GE} = 15 V; T_{VJ} = 25°C		2.3	2.7	V
	T_{VJ} = 125°C		2.7		V
$V_{GE(th)}$	I_C = 0.4 mA; V_{GE} = V_{CE}	4.5		6.5	V
I_{CES}	V_{CE} = V_{CES}; V_{GE} = 0 V; T_{VJ} = 25°C			0.6	mA
	T_{VJ} = 125°C		0.6		mA
I_{GES}	V_{CE} = 0 V; V_{GE} = ± 20 V			200	nA
$t_{d(on)}$			50		ns
t_r	Inductive load, T_{VJ} = 125°C		40		ns
$t_{d(off)}$	V_{CE} = 600 V; I_C = 10 A		290		ns
t_f	V_{GE} = ±15 V; R_G = 82 Ω		60		ns
E_{on}			1.2		mJ
E_{off}			1.1		mJ
C_{ies}	V_{CE} = 25 V; V_{GE} = 0 V; f = 1 MHz		600		pF
Q_{Gon}	V_{CE} = 600V; V_{GE} = 15 V; I_C = 10 A		45		nC
R_{thJC}	(per IGBT)			1.2	K/W

Output Inverter D1 - D6

Symbol	Conditions	Maximum Ratings	
I_{F25}	T_C = 25°C	25	A
I_{F80}	T_C = 80°C	15	A

Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
V_F	I_F = 10 A; V_{GE} = 0 V; T_{VJ} = 25°C		2.2	2.6	V
	T_{VJ} = 125°C		1.6		V
I_{RM}	I_F = 15 A; di_F/dt = -400 A/µs; T_{VJ} = 125°C		16		A
t_{rr}	V_R = 600 V; V_{GE} = 0 V		130		ns
R_{thJC}	(per diode)			2.1	K/W

Equivalent Circuits for Simulation

Conduction
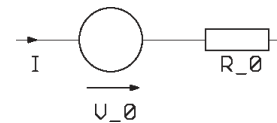
D11 - D16

Rectifier Diode (typ. at T_J = 125°C)
V_0 = 1.11 V; R_0 = 19 mΩ

T1 - T6 / D1 - D6

IGBT (typ. at V_{GE} = 15 V; T_J = 125°C)
V_0 = 1.32V; R_0 = 131 mΩ

Free Wheeling Diode (typ. at T_J = 125°C)
V_0 = 1.32 V; R_0 = 30 mΩ

T7 / D7

IGBT (typ. at V_{GE} = 15 V; T_J = 125°C)
V_0 = 1.32 V; R_0 = 131 mΩ

Free Wheeling Diode (typ. at T_J = 125°C)
V_0 = 1.39 V; R_0 = 56 mΩ

Thermal Response
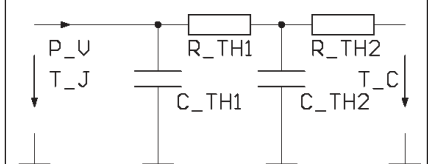
D11 - D16

Rectifier Diode (typ.)
C_{th1} = 0.093 J/K; R_{th1} = 1.212 K/W
C_{th2} = 0.778 J/K; R_{th2} = 0.258K/W

T1 - T6 / D1 - D6

IGBT (typ.)
C_{th1} = 0.09 J/K; R_{th1} = 0.954 K/W
C_{th2} = 0.809J/K; R_{th2} = 0.246 K/W

Free Wheeling Diode (typ.)
C_{th1} = 0.065 J/K; R_{th1} = 1.758 K/W
C_{th2} = 0.639 J/K; R_{th2} = 0.342 K/W

T7 / D7

IGBT (typ.)
C_{th1} = 0.09 J/K; R_{th1} = 0.954 K/W
C_{th2} = 0.809 J/K; R_{th2} = 0.246 K/W

Free Wheeling Diode (typ.)
C_{th1} = 0.043 J/K; R_{th1} = 2.738 K/W
C_{th2} = 0.54 J/K; R_{th2} = 0.462 K/W

Brake Chopper T7

Symbol	Conditions		Maximum Ratings	
V_{CES}	T_{VJ} = 25°C to 150°C		1200	V
V_{GES}	Continuous		± 20	V
V_{GEM}	Transient		± 30	V
I_{C25}	T_C = 25°C		20	A
I_{C80}	T_C = 80°C		15	A
RBSOA	V_{GE} = ±15 V; R_G = 82 Ω; T_{VJ} = 125°C Clamped inductive load; L = 100 µH	I_{CM} = 20 $V_{CEK} \leq V_{CES}$		A
t_{SC} (SCSOA)	V_{CE} = 720 V; V_{GE} = ±15 V; R_G = 82 Ω; T_{VJ} = 125°C non-repetitive		10	µs
P_{tot}	T_C = 25°C		105	W

B4

Symbol	Conditions	Characteristic Values (T_{VJ} = 25°C, unless otherwise specified)			
		min.	typ.	max.	
$V_{CE(sat)}$	I_C = 10 A; V_{GE} = 15 V; T_{VJ} = 25°C		2.3	2.7	V
	T_{VJ} = 125°C		2.7		V
$V_{GE(th)}$	I_C = 0.4 mA; $V_{GE} = V_{CE}$	4.5		6.5	V
I_{CES}	$V_{CE} = V_{CES}$; V_{GE} = 0 V; T_{VJ} = 25°C			0.5	mA
	T_{VJ} = 125°C		0.3		mA
I_{GES}	V_{CE} = 0 V; V_{GE} = ± 20 V			200	nA
$t_{d(on)}$			50		ns
t_r	Inductive load, T_{VJ} = 125°C		40		ns
$t_{d(off)}$	V_{CE} = 600 V; I_C = 10 A		290		ns
t_f	V_{GE} = ±15 V; R_G = 82 Ω		60		ns
E_{on}			1.2		mJ
E_{off}			1.1		mJ
C_{ies}	V_{CE} = 25 V; V_{GE} = 0 V; f = 1 MHz		600		pF
Q_{Gon}	V_{CE} = 600 V; V_{GE} = 15 V; I_C = 10 A		45		nC
R_{thJC}				1.2	K/W

Brake Chopper D7

Symbol	Conditions	Maximum Ratings	
V_{RRM}	T_{VJ} = 25°C to 150°C	1200	V
I_{F25}	T_C = 25°C	17	A
I_{F80}	T_C = 80°C	11	A

Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
V_F	I_F = 10 A; T_{VJ} = 25°C			2.9	V
	T_{VJ} = 125°C		1.9		V
I_R	$V_R = V_{RRM}$; T_{VJ} = 25°C			0.06	mA
	T_{VJ} = 125°C		0.07		mA
I_{RM}	I_F = 10 A; di_F/dt = -400 A/µs; T_{VJ} = 125°C		13		A
t_{rr}	V_R = 600 V		110		ns
R_{thJC}				3.2	K/W

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MUBW 10-12 A7

B4

Temperature Sensor NTC

Symbol	Conditions	min.	typ.	max.	
R_{25}	T = 25°C	4.75	5.0	5.25	kΩ
$B_{25/50}$			3375		K

Module

Symbol	Conditions	Maximum Ratings	
T_{VJ}	Operating	-40...+125	°C
T_{JM}		150	°C
T_{stg}		-40...+125	°C
V_{ISOL}	$I_{ISOL} \leq 1$ mA; 50/60 Hz	2500	V~
M_d	Mounting torque (M5)	2.7 - 3.3	Nm

Symbol	Conditions	min.	typ.	max.	
$R_{pin-chip}$			5		mΩ
d_S	Creepage distance on surface	6			mm
d_A	Strike distance in air	6			mm
R_{thCH}	with heatsink compound		0.02		K/W
Weight			180		g

Dimensions in mm (1 mm = 0.0394")

baseplate typ. 100 µm convex over 75 mm before monting
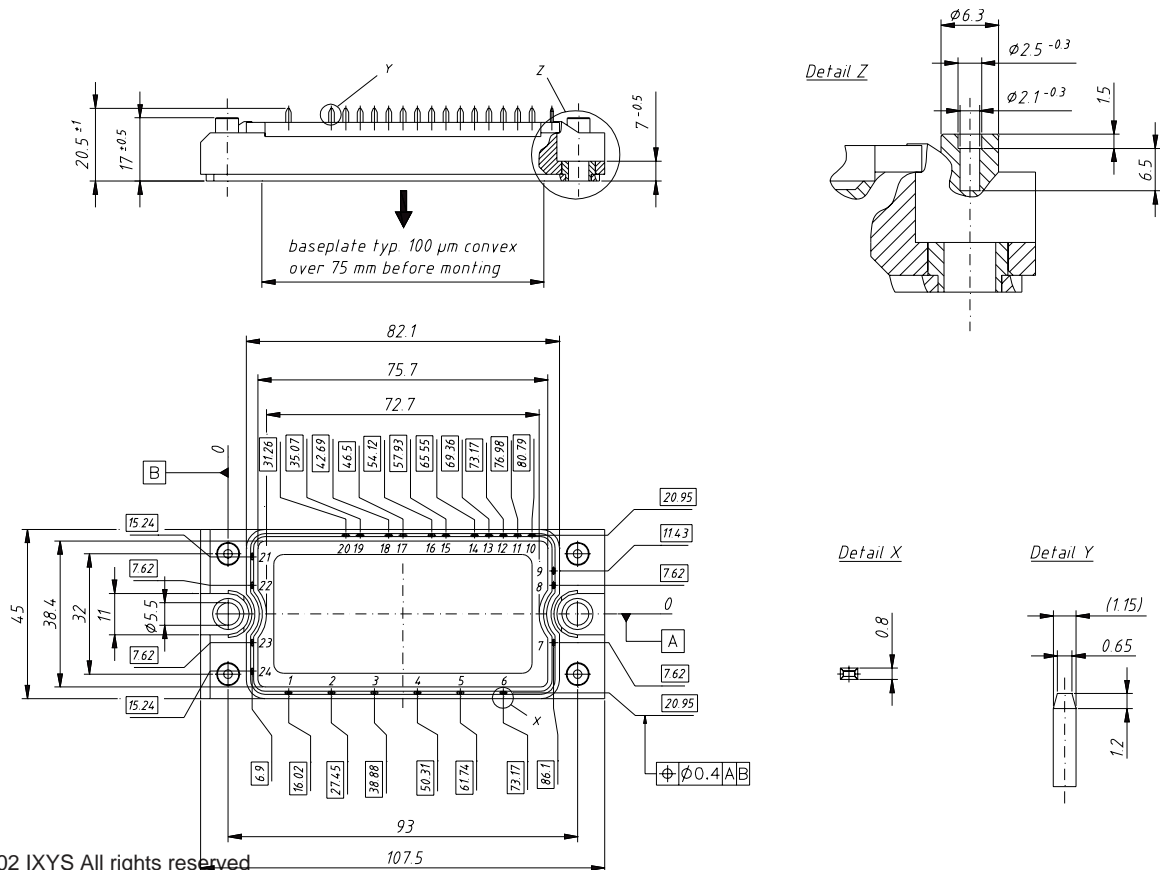
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Input Rectifier Bridge D11 - D16

B4
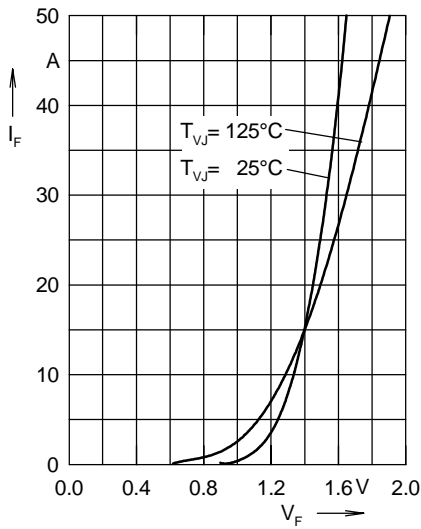
Fig. 1 Forward current versus voltage drop per diode
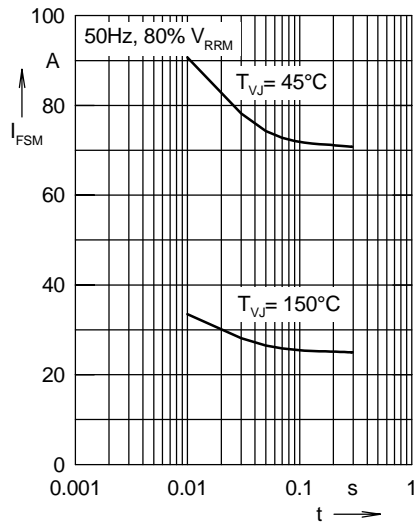
Fig. 2 Surge overload current
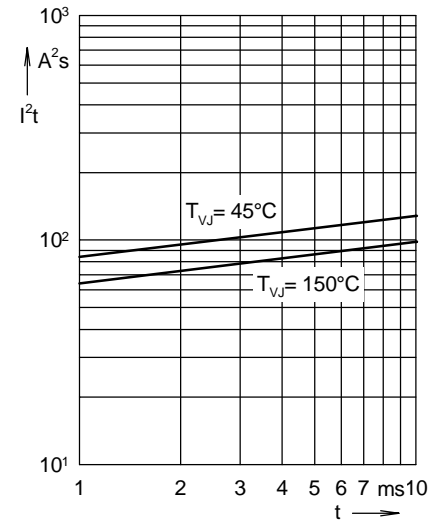
Fig. 3 I^2t versus time per diode
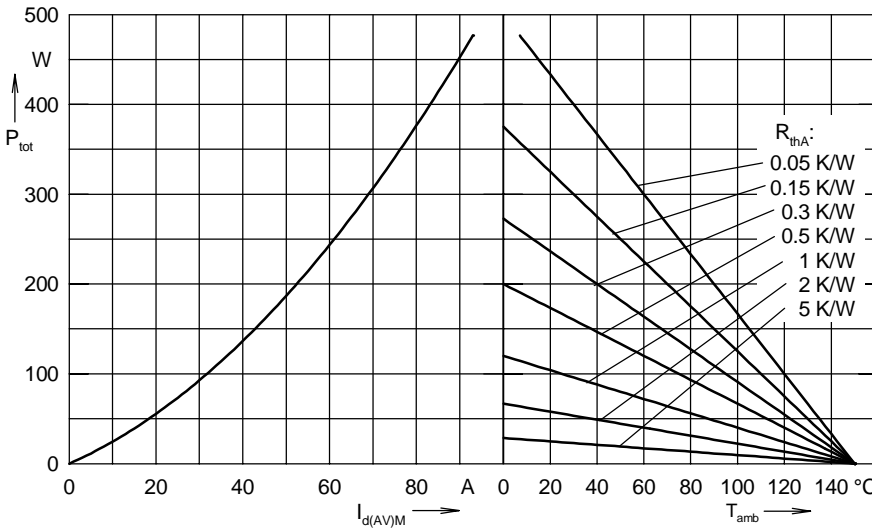
Fig. 4 Power dissipation versus direct output current and ambient temperature, sin 180°
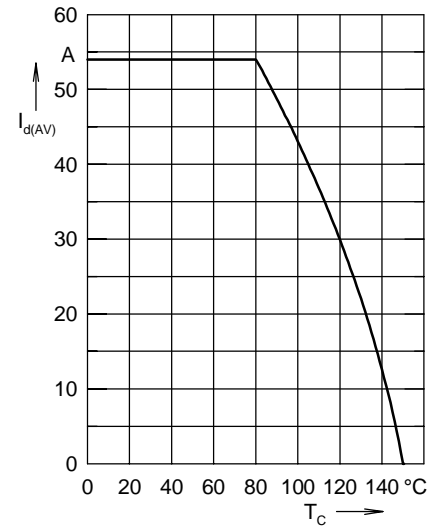
Fig. 5 Max. forward current versus case temperature
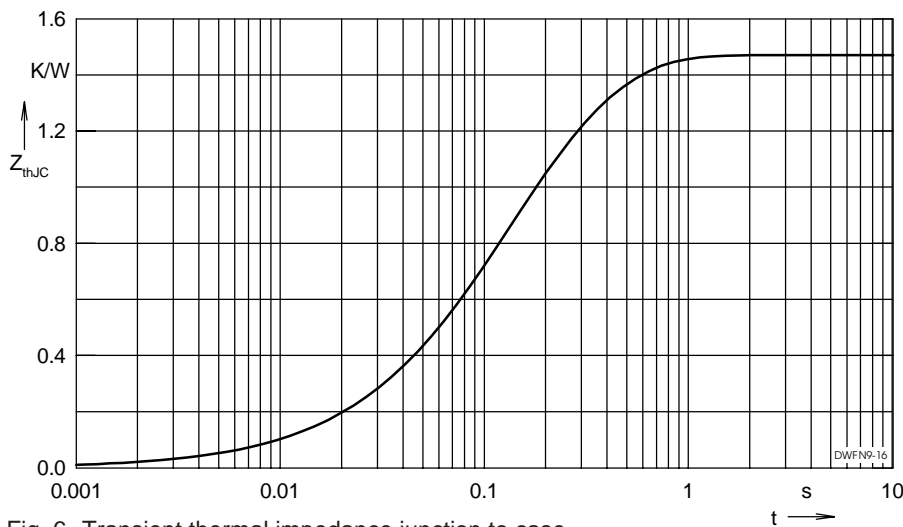
Fig. 6 Transient thermal impedance junction to case

Output Inverter T1 - T6 / D1 - D6
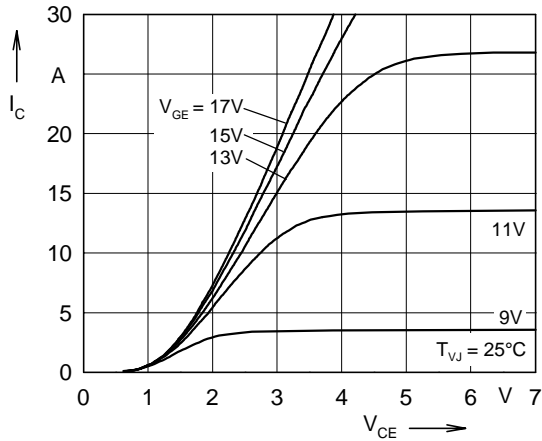
Fig. 7 Typ. output characteristics
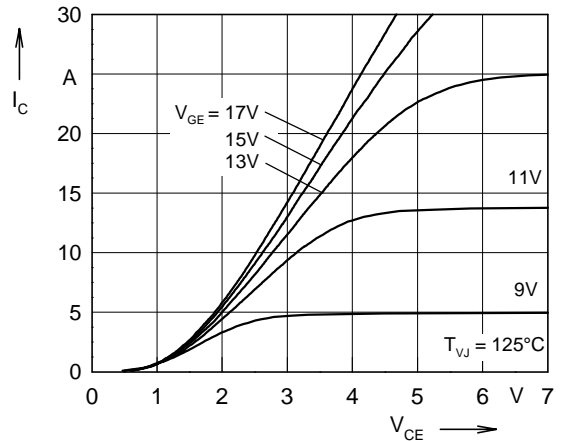
Fig. 8 Typ. output characteristics

B4
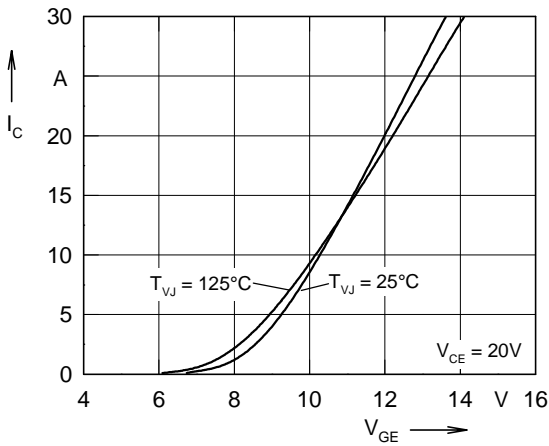
Fig. 9 Typ. transfer characteristics
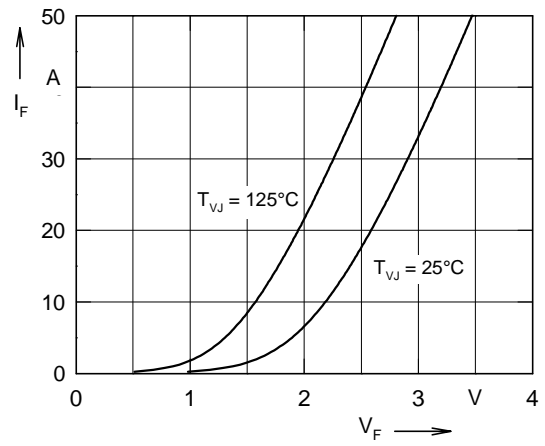
Fig. 10 Typ. forward characteristics of free wheeling diode
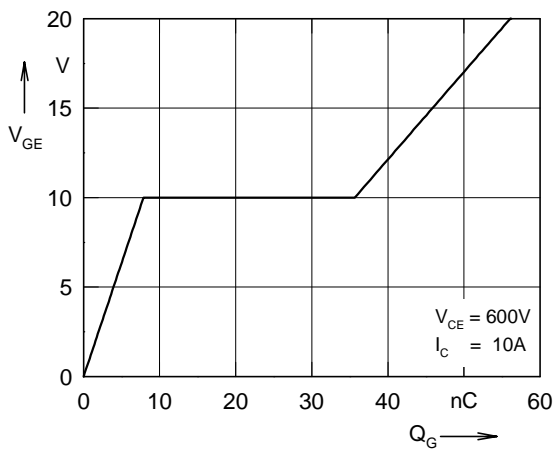
Fig. 11 Typ. turn on gate charge
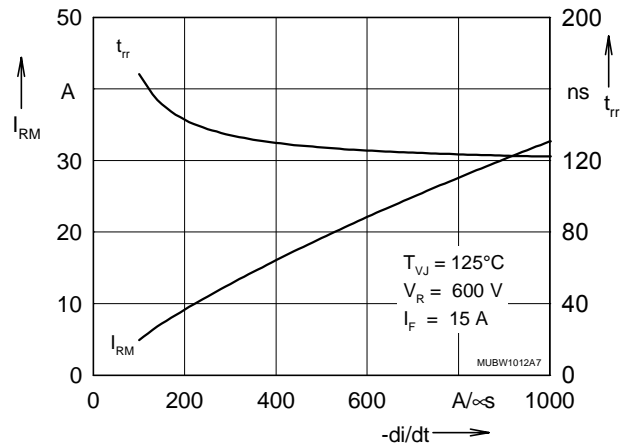
Fig. 12 Typ. turn off characteristics of free wheeling diode

Output Inverter T1 - T6 / D1 - D6
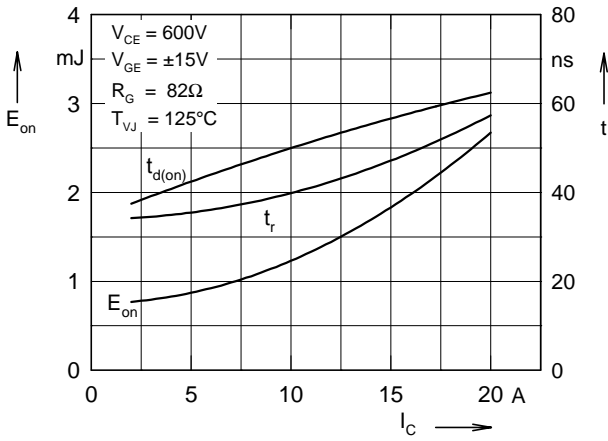
Fig. 13 Typ. turn on energy and switching
times versus collector current
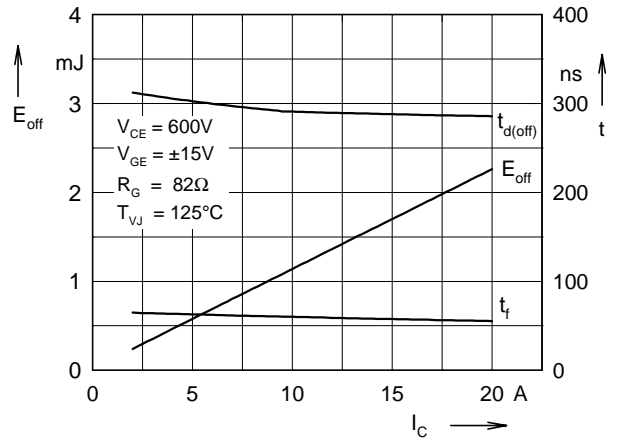
Fig. 14 Typ. turn off energy and switching
times versus collector current
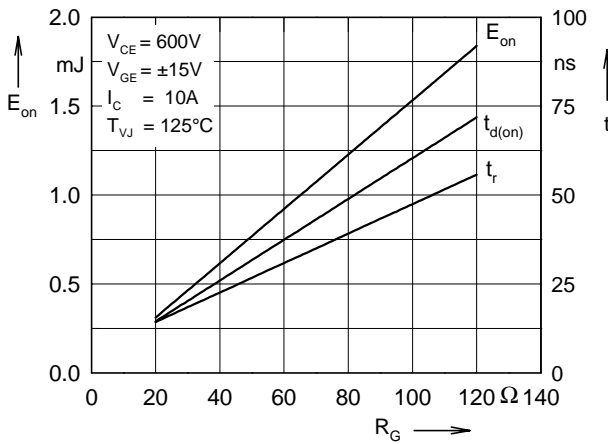
Fig. 15 Typ. turn on energy and switching
times versus gate resistor
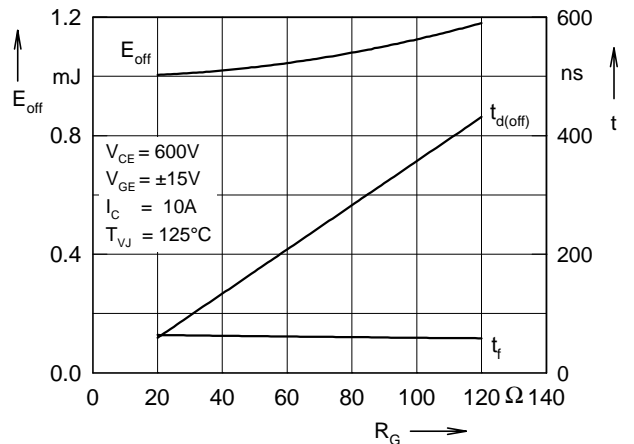
Fig.16 Typ. turn off energy and switching
times versus gate resistor
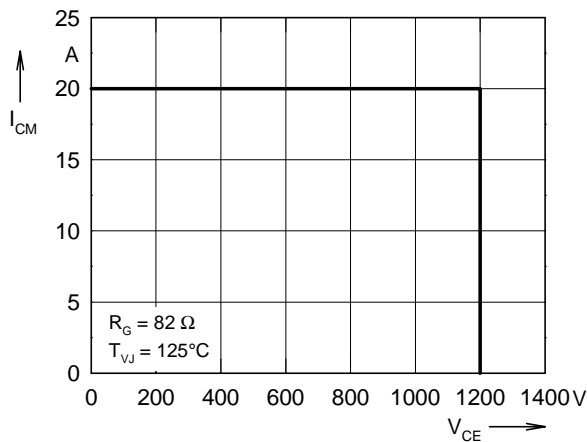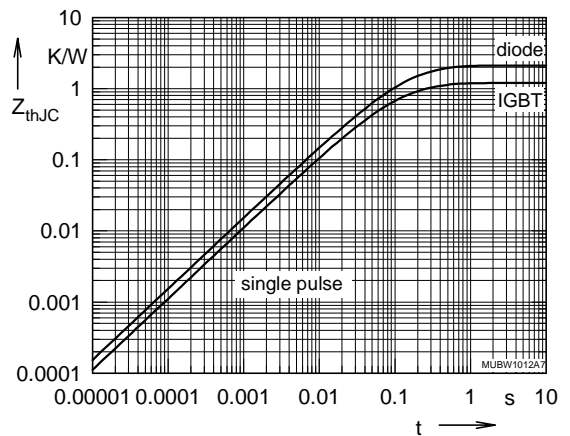
Fig. 17 Reverse biased safe operating area
RBSOA

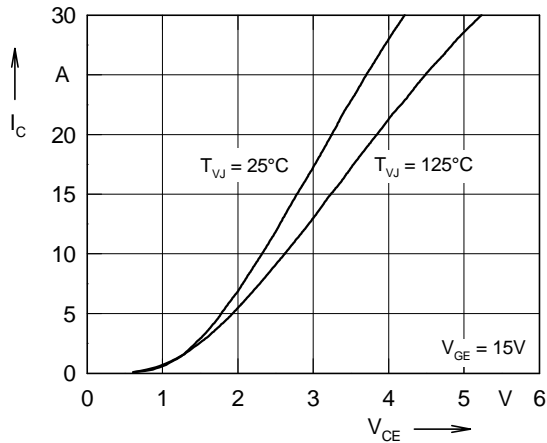Fig. 18 Typ. transient thermal impedance

Brake Chopper T7 / D7

B4

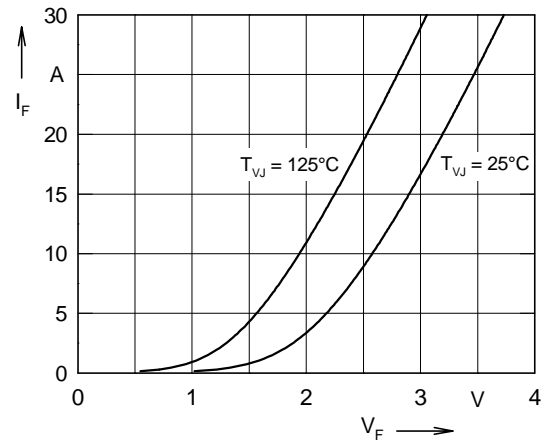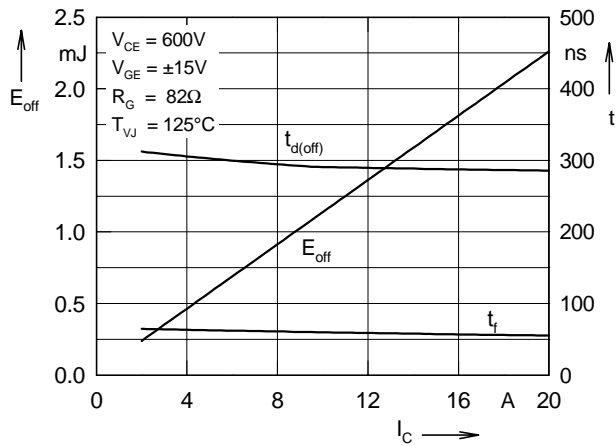Fig. 19 Typ. output characteristics

Fig. 20 Typ. forward characteristics of free wheeling diode

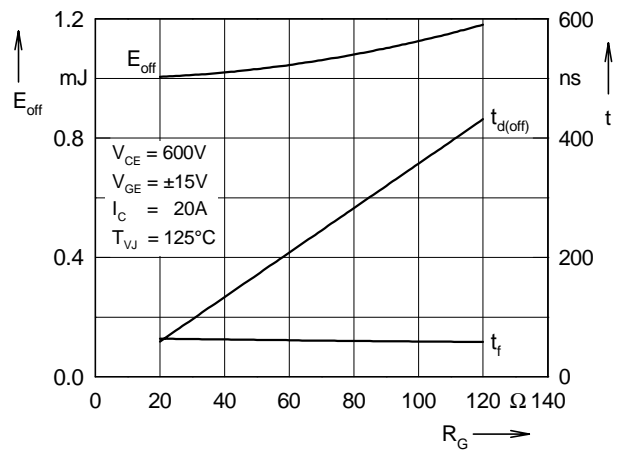Fig. 21 Typ. turn off energy and switching times versus collector current

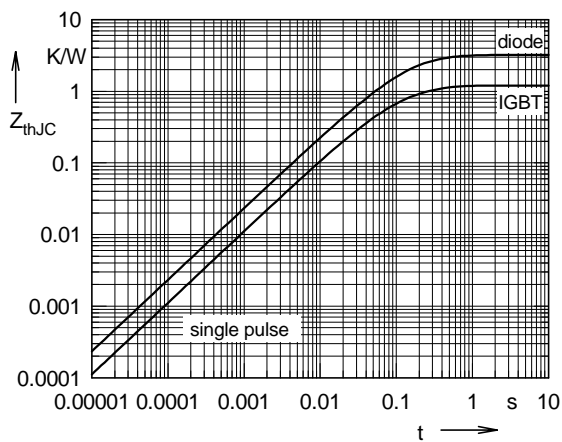Fig. 22 Typ. turn off energy and switching times versus gate resistor

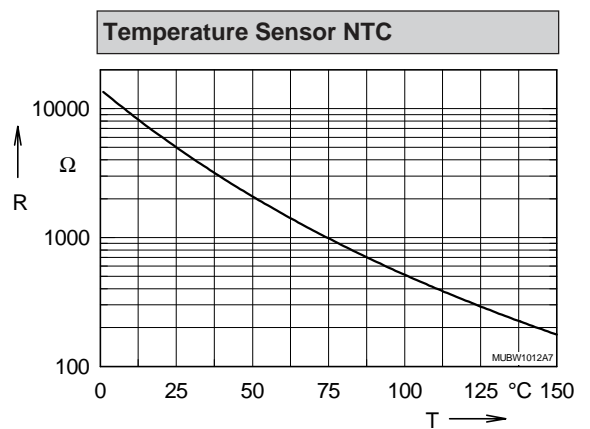Fig. 23 Typ. transient thermal impedance

Temperature Sensor NTC

Fig. 24 Typ. thermistorresistance versus temperature